

## isc Silicon NPN Power Transistor

2SC4461

## DESCRIPTION

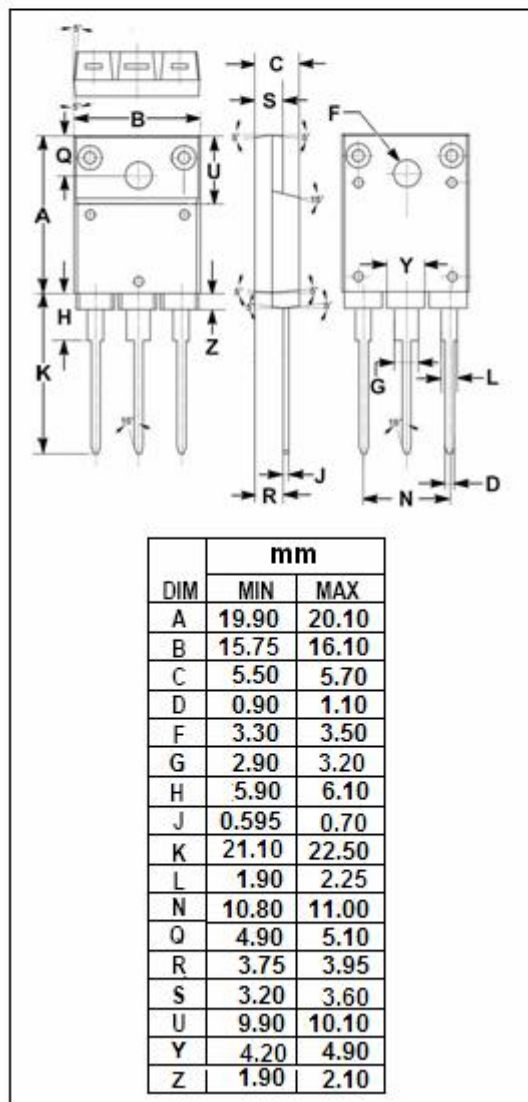
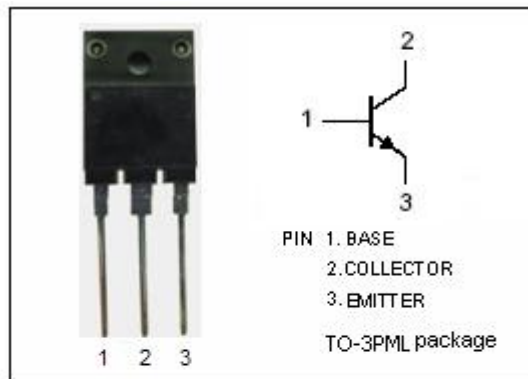
- High Breakdown Voltage-  
:  $V_{(BR)CEO} = 500V(\text{Min})$
- Fast Switching speed
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

- Designed for switching regulator applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	800	V
$V_{CEO}$	Collector-Emitter Voltage	500	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	25	A
$I_{CP}$	Collector Current-Pulse	40	A
$I_B$	Base Current-Continuous	8	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	65	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	3	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistor****2SC4461****ELECTRICAL CHARACTERISTICS****T<sub>C</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 5mA; R <sub>BE</sub> = ∞	500			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	800			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	7			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 12A; I <sub>B</sub> = 2.4A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 12A; I <sub>B</sub> = 2.4A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 500V; I <sub>E</sub> = 0			10	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			10	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 2.4A ; V <sub>CE</sub> = 5V	15		50	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 12A ; V <sub>CE</sub> = 5V	8			
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz		260		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 2.4A ; V <sub>CE</sub> = 10V		18		MHz

**◆ h<sub>FE-1</sub> Classifications**

L	M	N
15-30	20-40	30-50

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